

Features: (typical values)

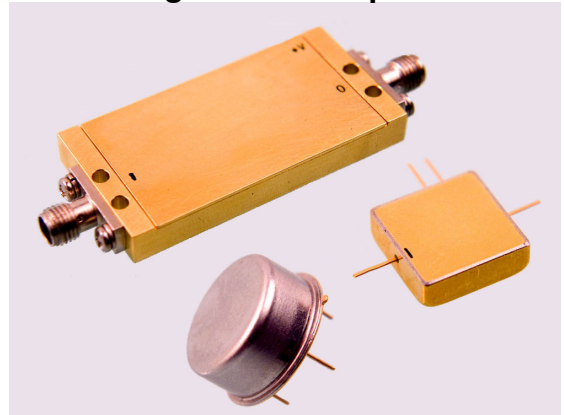
- Low Noise Figure 3.2 dB.
- High Output Power +27.0 dBm.
- High IP3 +42 dBm.

Maximum Ratings

Storage Temperature -62°C to +125°C
 DC Voltage +15 volts
 RF Input Power +13.0 dBm.
 Case Temperature +125°C
 Max. Short Term RF Input Power (1 minute)..... 50mW

Specifications (Referenced to 50 ohms)

**1-200 MHz
High Power Amplifier**



Parameter	Typical Conditions	Min Value	Max Value	Units
Frequency		1	200	MHz.
Gain	18.4	16.0		dB.
Gain Flatness	±0.2		±1.0	dB.
Pout @ 1dB Comp	+27.0	+24.0		dBm.
Noise Figure	3.2		5.0	dB.
Reverse Isolation	20.0			dB.
IP2	+76.0			dBm.
IP3 (two-tone)*	+42.0			dBm.
Second Order Harmonic IP	80.0			dBm.
VSWR In/Out	1.5:1		1.9:1	Ratio
Supply Required	+15/155		+15/180	v/mA.

Min. and max. values are from -55°C to +85°C

*IP3 is an in band output intercept point @ +15 dBm. Per tone

